

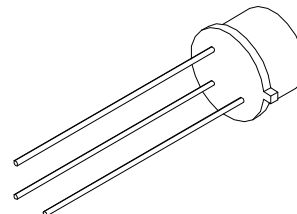


PRELIMINARY

**SOLID STATE DEVICES, INC.**14005 Stage Road \* Santa Fe Springs, Ca 90670  
Phone: (562) 404-4474 \* Fax: (562) 404-1773**SFT5333****2 AMP  
100 VOLTS  
HIGH SPEED  
PNP TRANSISTOR****DESIGNER'S DATA SHEET****FEATURES:**

- Radiation Tolerant
- Fast Switching, 150ns MAX t(on)
- High Frequency, fT 85MHz MIN.
- BVCEO 70Volts MIN.
- Low Saturation Voltage.
- 200°C Operating, Gold Eutectic Die Attach.
- Designed for Complementary Use with SFT4300.

TO-5



MAXIMUM RATINGS	SYMBOL	VALUE	UNITS
Collector-Emitter Voltage	$V_{CEO}$	70	Volts
Collector-Base Voltage	$V_{CBO}$	100	Volts
Emitter-Base Voltage	$V_{EBO}$	6	Volts
Collector Current	$I_C$	2	Amps
Base Current	$I_B$	1	Amps
Total Device Dissipation @ $T_C=100^\circ\text{C}$ Derate above 100°C	$P_D$	6.6 66	W mW/°C
Operating and Storage Temperature	$T_J, T_{STG}$	-65 to +200	°C
Thermal Resistance, Junction to Case	$R_{qJC}$	15.2	°C/W

ELECTRICAL CHARACTERISTICS	SYMBOL	MIN	MAX	UNITS
Collector-Emitter Breakdown Voltage ( $I_C = 30 \text{ mA}_{DC}$ )	$BV_{CEO}$	70	-	Volts
Collector-Base Breakdown Voltage ( $I_C = 200 \mu\text{A}_{DC}$ )	$BV_{CBO}$	100	-	Volts
Emitter-Base Breakdown Voltage ( $I_E = 200 \mu\text{A}_{DC}$ )	$BV_{EBO}$	6	-	Volts
Collector Cutoff Current ( $V_{CB} = 90V_{DC}, T_C = 25^\circ\text{C}$ ) ( $V_{CB} = 90V_{DC}, T_C = 100^\circ\text{C}$ )	$I_{CBO}$	-	1 75	mA mA
Collector Cutoff Current ( $V_{CE} = 40 V_{DC}$ )	$I_{CEO}$	-	5	mA

NOTE: All specifications are subject to change without notification.  
SCD's for these devices should be reviewed by SSDI prior to release.**DATA SHEET #: TR0002C**

# SFT5333

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ELECTRICAL CHARACTERISTICS		SYMBOL	MIN	MAX	UNITS
Emitter Cutoff Current ( $V_{EB} = 6V_{DC}$ )		$I_{EBO}$	-	1	mA
DC Current Gain * ( $I_C = 1.0 A_{DC}$ , $V_{CE} = 5 V_{DC}$ ) ( $I_C = 2.0 A_{DC}$ , $V_{CE} = 5 V_{DC}$ )		$H_{FE}$	40 40	250	
Collector-Emitter Saturation Voltage * ( $I_C = 1.0 A_{DC}$ , $I_B = 100 mA_{DC}$ ) ( $I_C = 2.0 A_{DC}$ , $I_B = 200 mA_{DC}$ )		$V_{CE(SAT)}$	- -	0.45 1.0	Volts
Base-Emitter Voltage * ( $I_C = 2.0 A_{DC}$ , $V_{CE} = 4 V_{DC}$ )		$V_{BE(ON)}$	-	1.5	Volts
Current Gain Bandwidth Product ( $I_C = 1.0 A_{DC}$ , $V_{CE} = 10 V_{DC}$ , $f = 10 MHz$ )		fT	85	-	MHz
Output Capacitance ( $V_{CB} = 30V_{DC}$ , $I_E = 0A_{DC}$ , $f = 1.0MHz$ )		$C_{ob}$	-	75	pF
Input Capacitance ( $V_{BE} = 6V_{DC}$ , $I_C = 0A_{DC}$ , $f = 1.0MHz$ )		$C_{ib}$	-	300	pF
Turn On Time	( $V_{CC} = 20V_{DC}$ , $I_C = 1.0A_{DC}$ , $V_{EB(OFF)} = 3.7V_{DC}$ , $I_{B1} = I_{B2} = 100mA_{DC}$ , $R_L = 20 Ohms$ )	$t_{(on)}$	-	150	ns
Turn Off Time		$t_{(off)}$	-	450	ns

\*Pulse Test: Pulse Width = 300ms, Duty Cycle = 2%

## CASE OUTLINE: TO-5

- PIN 1: EMITTER
- PIN 2: BASE
- PIN 3: COLLECTOR

